

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-7. (Canceled)

8. (Currently Amended) A method for manufacturing a thin film transistor, ~~characterized by comprising said method comprising:~~

forming a semiconductor film over an insulating substrate;

forming a first insulating film over the semiconductor film;

heat-treating the semiconductor film and the first insulating film;

patterning the semiconductor film and the first insulating film into island shapes with the use of the same photomask after ~~the heat treatment~~ heat-treating the semiconductor film and the first insulating film to form an island-shaped semiconductor film and an island-shaped gate insulating film;

forming a second insulating film over the island-shaped gate insulating film;

etching the second insulating film anisotropically to form a side wall covering side faces of the island-shaped semiconductor film and the island-shaped gate insulating film in self-aligned manner;

forming a conductive film over the island-shaped gate insulating film after forming the side wall; and

patterning the conductive film to form a gate electrode.

9. (Currently Amended) A method for manufacturing a thin film transistor, ~~characterized by comprising said method comprising:~~

forming a semiconductor film over an insulating substrate;

forming an insulating film over the semiconductor film;

heat-treating the semiconductor film and the insulating film;

patterning the semiconductor film and the insulating film into island shapes with the use of one resist mask after ~~the heat treatment~~ heat-treating the semiconductor film and the insulating film to form an island-shaped semiconductor film and an island-shaped gate insulating film;

insulating a side face of the semiconductor film by adding oxygen or nitrogen to a side face of the island-shaped semiconductor film without removing the resist mask;

forming a conductive film over the island-shaped gate insulating film; and

patterning the conductive film to form a gate electrode.

10. (Currently Amended) A method for manufacturing a thin film transistor, ~~characterized by comprising~~ said method comprising:

forming a semiconductor film over an insulating substrate;

forming a first insulating film over the semiconductor film;

heat-treating the semiconductor film and the first insulating film;

patterning the semiconductor film and the first insulating film into island shapes with the use of the same photomask after ~~the heat treatment~~ heat-treating the semiconductor film and the first insulating film to form an island-shaped semiconductor film and an island-shaped gate insulating film;

forming a second insulating film over the island-shaped gate insulating film;

patterning the second insulating film to cover edge portions of the island-shaped semiconductor film and the island-shaped gate insulating film and only a peripheral portion of a top face of the island-shaped gate insulating film;

forming a conductive film over the island-shaped gate insulating film; and

patterning the conductive film to form a gate electrode.

11. (Currently Amended) A method for manufacturing a thin film transistor, ~~characterized by comprising~~ said method comprising:

forming a semiconductor film over an insulating substrate;
forming a first insulating film over the semiconductor film;
forming a first conductive film over the first insulating film;
heat-treating the semiconductor film, the first insulating film, and the first conductive film,

patterning the semiconductor film, the first insulating film, and the first conductive film into island shapes with the use of the same photomask after ~~the heat treatment~~ heat-treating the semiconductor film, the first insulating film, and the first conductive film to form an island-shaped semiconductor film, an island-shaped gate insulating film, and a first island-shaped conductive film;

forming a second insulating film over the first island-shaped conductive film;

etching the second insulating film anisotropically to form a side wall covering side faces of the island-shaped semiconductor film, the island-shaped gate insulating film, and the first island-shaped conductive film in a self-aligned manner;

forming a second conductive film over the first island-shaped conductive film after forming the side wall; and

patterning the first island-shaped conductive film and the second conductive film to form a gate electrode.

12. (Currently Amended) A method for manufacturing a thin film transistor, ~~characterized by comprising~~ said method comprising:

forming a semiconductor film over an insulating substrate;
forming an insulating film over the semiconductor film;
forming a first conductive film over the insulating film;
heat-treating the semiconductor film, the insulating film, and the first conductive film;

patterning the semiconductor film, the insulating film, and the first conductive film into island shapes with the use of the same resist mask after ~~the heat treatment~~ heat-

treating the semiconductor film, the insulating film, and the first conductive film to form an island-shaped semiconductor film, an island-shaped gate insulating film, and a first island-shaped conductive film;

adding oxygen or nitrogen to a side face of the island-shaped semiconductor film without removing the resist mask to insulate a side face of the semiconductor film;

forming a second conductive film over the first island-shaped conductive film; and

patterning the first island-shaped conductive film and the second conductive film to form a gate electrode.

13. (Currently Amended) A method for manufacturing a thin film transistor, ~~characterized by comprising~~ said method comprising:

forming a semiconductor film over an insulating substrate;

forming a first insulating film over the semiconductor film;

forming a first conductive film over the insulating film;

heat-treating the semiconductor film, the first insulating film, and the first conductive film;

patterning the semiconductor film, the first insulating film, and the first conductive film into island shapes with the use of the same photomask after ~~the heat treatment~~ heat-treating the semiconductor film, the first insulating film, and the first conductive film to form an island-shaped semiconductor film, an island-shaped gate insulating film, and a first island-shaped conductive film;

forming a second insulating film over the first island-shaped conductive film;

patterning the second insulating film to cover edge portions of the island-shaped semiconductor film, the island-shaped gate insulating film, and the first island-shaped conductive film and only a peripheral portion of a top face of the first island-shaped conductive film;

forming a second conductive film over the island-shaped gate insulating film; and

forming a gate electrode by patterning the first conductive film and the second conductive film.

14. (Currently Amended) A method for manufacturing a thin film transistor according to any one of claims 8, 10, 11 and 13, ~~characterized in that~~ wherein the ~~heat-treatment of~~ heat-treating the semiconductor film and the first insulating film is done at a temperature of from 600 °C to 800 °C.

15. (Currently Amended) A method for manufacturing a thin film transistor according to claim 9 or 12, ~~characterized in that~~ wherein the ~~heat-treatment of~~ heat-treating the semiconductor film and the insulating film is done at a temperature of from 600 °C to 800 °C.

16. (Currently Amended) A method for manufacturing a thin film transistor according to claim 14, ~~characterized in that~~ wherein a strain point of the insulating substrate is equal to or lower than 600 °C.

17. (Currently Amended) A method for manufacturing a thin film transistor according to claim 15, ~~characterized in that~~ wherein a strain point of the insulating substrate is equal to or lower than 600 °C.

18. (Currently Amended) A method for manufacturing a thin film transistor according to claim 9, ~~characterized in that~~ wherein the gate electrode is led outside the island-shaped semiconductor film.

19. (Currently Amended) A method for manufacturing a thin film transistor according to claim 10, ~~characterized in that~~ wherein the gate electrode is led outside the island-shaped semiconductor film.

20. (Currently Amended) A method for manufacturing a thin film transistor according to claim 11, ~~characterized in that~~ wherein the gate electrode is led outside the island-shaped semiconductor film.

21. (Currently Amended) A method for manufacturing a thin film transistor according to claim 12, ~~characterized in that~~ wherein the gate electrode is led outside the island-shaped semiconductor film.

22. (Currently Amended) A method for manufacturing a thin film transistor according to claim 13, ~~characterized in that~~ wherein the gate electrode is led outside the island-shaped semiconductor film.

23. (Canceled)